

**4A 4Quadrants TRIACs**
**Product Summary**

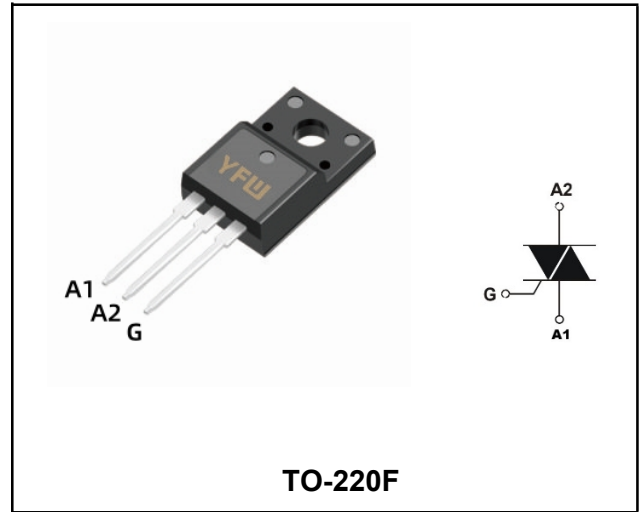
Symbol	Value	Unit
$I_{T(RMS)}$	4	A
$V_{DRM} V_{RRM}$	600/800	V
$V_{TM}$	1.55	V

**Features**

With high ability to withstand the shock loading of large current, Provide high dv/dt rate with strong resistance to electromagnetic interference.

**Application**

Power charger, T-tools, massager, solid state relay, AC Motor speed regulation and so on.


**Absolute maximum ratings (Ta=25°C unless otherwise noted)**

Parameter	Symbol	Value	Unit	
Repetitive peak off-state voltage	$V_{DRM}$	600/800	V	
Repetitive peak reverse voltage	$V_{RRM}$	600/800	V	
RMS on-state current	$I_{T(RMS)}$	4	A	
Non repetitive surge peak on-state current	$I_{TSM}$	25	A	
$I^2t$ value for fusing (tp=10ms)	$I^2t$	3.1	A <sup>2</sup> s	
Critical rate of rise of on-state current ( $I_G = 2 \times I_{GT}$ )	$dI_T/dt$	I - II - III	50	A/ $\mu$ s
		IV	10	
Peak gate current	$I_{GM}$	2	A	
Average gate power dissipation	$P_G (AV)$	5	W	
Junction Temperature	$T_J$	-40~+125	°C	
Storage Temperature	$T_{STG}$	-40 ~+150	°C	

**Electrical characteristics (TA=25°C, unless otherwise noted)**

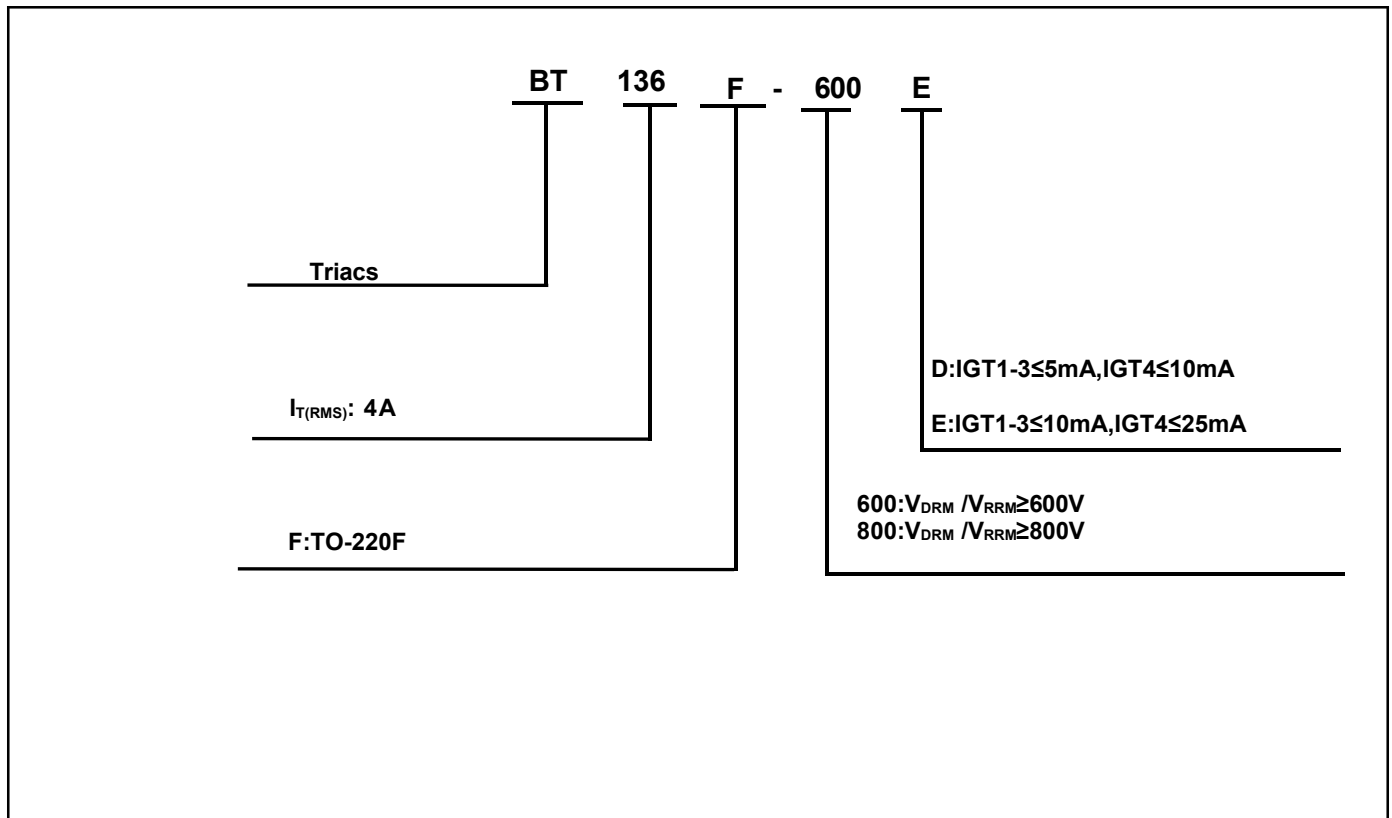
Parameter	Symbol	Test Condition	Value		Unit	
			D	E		
Gate trigger current	I <sub>GT</sub>	V <sub>D</sub> =12V, I <sub>T</sub> =0.1A, T <sub>j</sub> =25°C, Fig. 6	I - II - III	≤5	≤10	mA
			IV	≤10	≤25	mA
Gate trigger voltage	V <sub>GT</sub>	I - II - III - IV	≤1.3		V	
Non-triggering gate voltage	V <sub>GD</sub>	V <sub>D</sub> =V <sub>DRM</sub> T <sub>j</sub> =125°C	≥0.2		V	
Holding current	I <sub>H</sub>	V <sub>D</sub> =12V, I <sub>GT</sub> =0.1A, T <sub>j</sub> =25°C, Fig. 6	I - II - III - IV	≤10	≤15	mA
Latching current	I <sub>L</sub>	I - III - IV	≤10	≤15	mA	
			II	≤15		≤20
Critical-rate of rise of commutation voltage	dV <sub>D</sub> /dt	V <sub>D</sub> =67%V <sub>DRM</sub> , T <sub>j</sub> =125°C	≥10	≥20	V/μs	

**STATIC CHARACTERISTICS**

On-state Voltage	V <sub>TM</sub>	I <sub>TM</sub> =6A, tp=380μs, Fig. 4	≤1.55		V	
Repetitive Peak Off-State Current	I <sub>DRM</sub>	V <sub>D</sub> =V <sub>DRM</sub> = V <sub>R</sub> RM	T <sub>j</sub> =25°C	≤10	10	μA
Repetitive Peak Reverse Current	I <sub>RRM</sub>		T <sub>j</sub> =125°C	≤1	≤01	mA

**THERMAL RESISTANCES**

Thermal resistance	R <sub>th(j-c)</sub>	Junction to case	TYP.	4.0	°C/W
	R <sub>th(j-a)</sub>	Junction to ambient	TYP.	60	°C/W

**Ordering Information**


**Typical Characteristics**

FIG1 Maximum power dissipation versus RMS on-state current

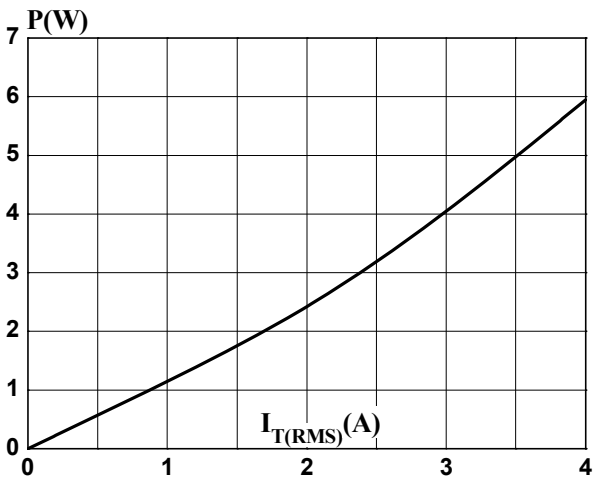


FIG3 Surge peak on-state current versus number of cycles

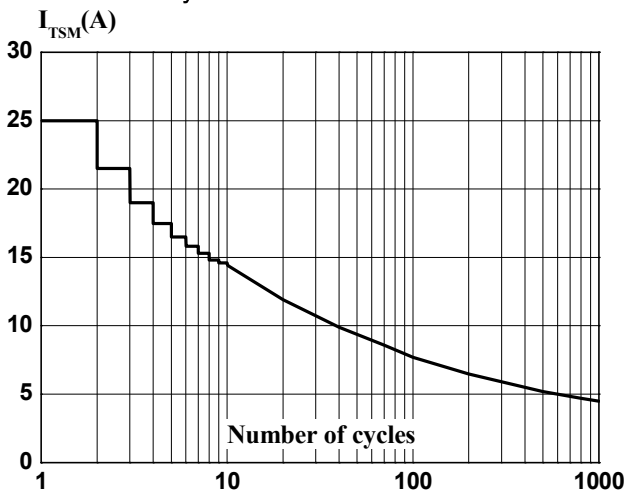


FIG5 Non-repetitive surge peak on-state current for a sinusoidal pulse with width  $t_p < 20\text{ms}$ , and corresponding value of  $I^2t$  ( $dI/dt < 100\text{A}/\mu\text{s}$ )

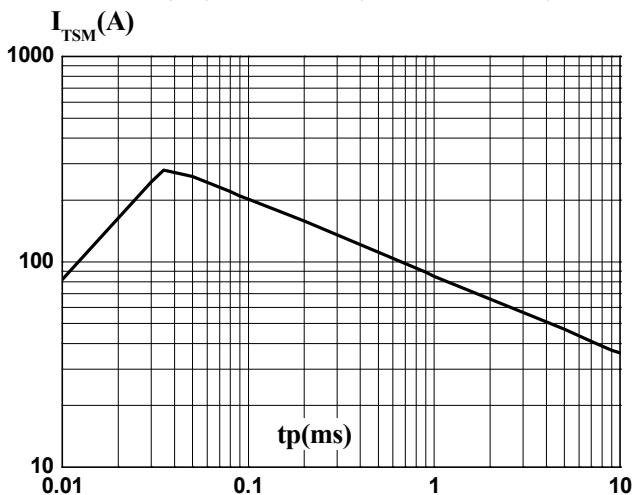


FIG2 RMS on-state current versus case temperature

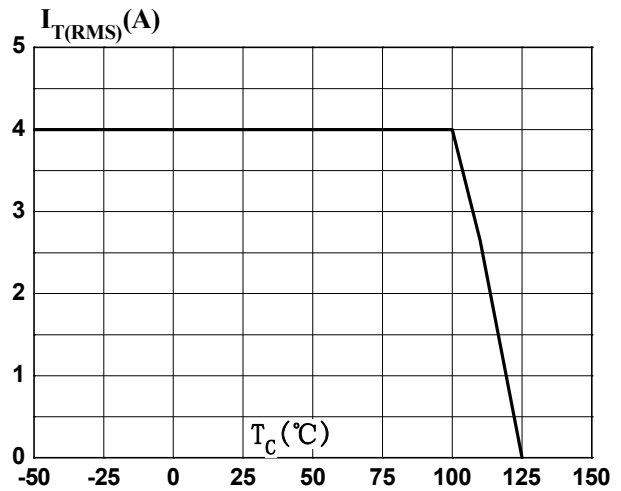


FIG4 On-state characteristics (maximum values)

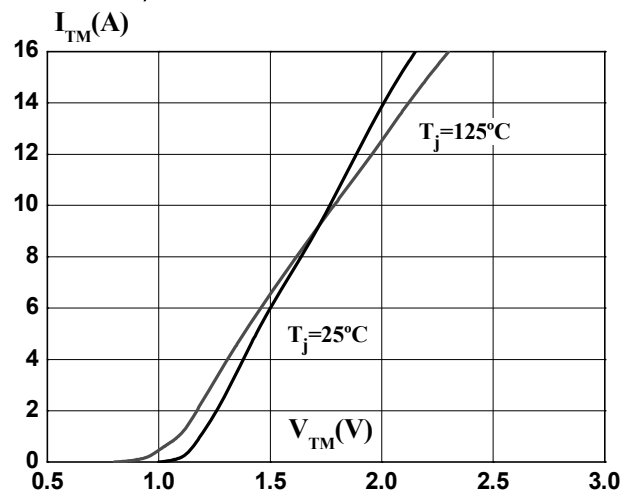
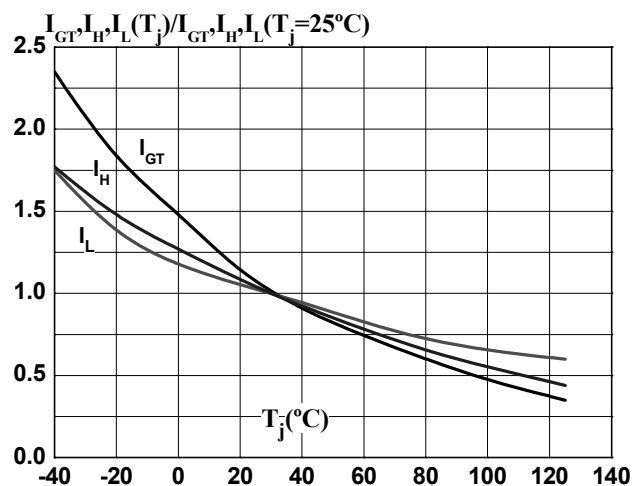
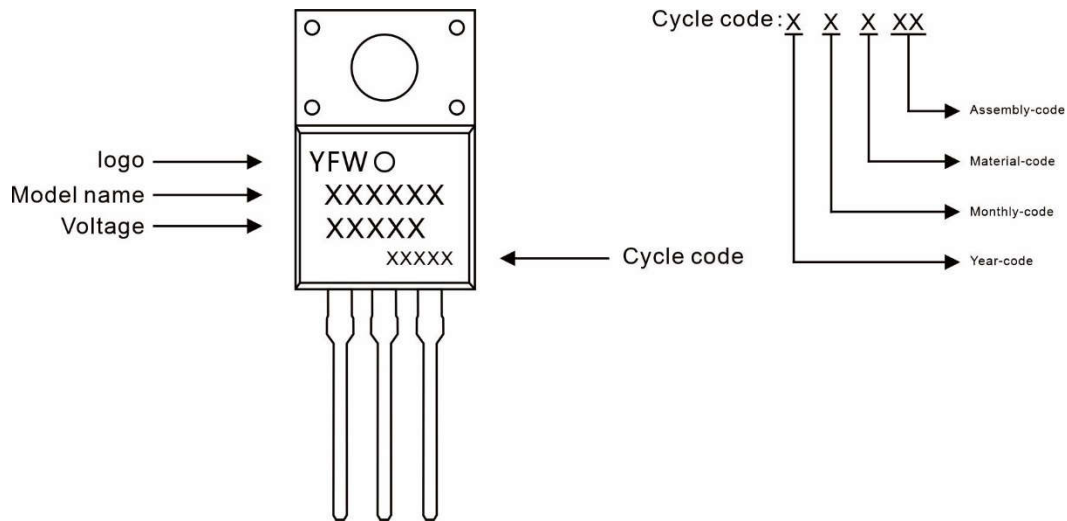


FIG6 Relative variations of gate trigger current, holding current and latching current versus junction temperature



**Marking Diagram**



**Ordering information**

Model name	Package	Unit Weight	Base Quantity	Packing Quantity
BT136F	TO-220F	0.06oz(1.74g)	50pcs/tube	1000PCS/Box 5000PCS/Carton

**Package Dimensions**

**TO-220F**

Symbol	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	4.50	4.90	0.177	0.193
A1	2.34	2.74	0.092	0.108
A2	2.66	2.86	0.105	0.113
b	0.75	0.85	0.030	0.033
b1	1.24	1.44	0.049	0.057
c	0.40	0.60	0.016	0.024
D	10.00	10.32	0.394	0.406
E	15.75	16.05	0.620	0.632
e	2.44	2.64	0.096	0.104
e1	4.88	5.28	0.192	0.208
F	3.10	3.5	0.122	0.138
L	13.50	13.90	0.531	0.547
L1	2.90	3.30	0.114	0.130
Φ	3.10	3.30	0.122	0.130

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